

DTC115GUA / DTC115GKA

- 1) The built-in bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 2) Only the on / off conditions need to be set for operation, making device design easy.
- 3) Higher mounting densities can be achieved.

E : Emitter
C : Collector
B : Base

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	50	V
Collector-emitter voltag	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

Type	DTC115GUA	DTC115GKA
Package	UMT3	SMT3
Marking	K29	K29
Packaging code	T106	T146
Basic ordering unit (pieces)	3000	3000

- (1) Emitter
- (2) Base
- (3) Collector

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Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	50	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=72\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=50V$
Emitter cutoff current	I_{EBO}	30	—	58	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C=5mA, I_E=0.25mA$
DC current transfer ratio	h_{FE}	82	—	—	—	$I_C=5mA, V_{CE}=5V$
Emitter-base resistance	R	70	100	130	$k\Omega$	—
Transition frequency	f_T	—	250	—	MHz	$V_{CE}=10V, I_E=-5mA, f=100MHz$

* Transition frequency of the device.